

General Description

The MAX4558/MAX4559/MAX4560 are low-voltage, CMOS analog ICs configured as an 8-to-1 multiplexer (MAX4558), a dual 4-to-1 multiplexer (MAX4559), and a triple single-pole/double-throw (SPDT) switch (MAX4560). Each switch is protected against ±15kV electrostatic discharge (ESD) shocks, without latchup or damage.

These CMOS devices can operate continuously from dual supplies of ±2V to ±6V or from a +2V to +12V single supply. Each switch can handle Rail-to-Rail® analog signals. The off-leakage current is only 1nA at +25℃ or 10nA at +85℃ max.

All digital inputs have +0.8V to +2.4V logic thresholds, ensuring TTL/CMOS-logic compatibility when using a single +5V supply or dual ±5V supplies.

Applications

Battery-Operated Equipment Audio and Video Signal Routing Low-Voltage Data-Acquisition Systems Communications Circuits **High-ESD Environments**

Features

- ESD-Protected X, Y, Z and X_, Y_, Z_ Pins ±15kV (Human Body Model) ±12kV (IEC 1000-4-2, Air-Gap Discharge) ±8kV (IEC 1000-4-2, Contact Discharge)
- **♦** Pin-Compatible with Industry-Standard 74HC4051/74HC4052/74HC4053
- → Guaranteed On-Resistance 220 Ω with Single +5V Supply 160 Ω with ±5V Supply
- ♦ Ron Match Between Channels: 2Ω (typ)
- ♦ Guaranteed Low leakage Currents 1nA Off-Leakage (at +25°C) 1nA On-Leakage (at +25°C)
- ♦ TTL-Compatible Inputs with +5V/±5V Supplies
- **♦** Low Distortion: < 0.02% (600Ω)
- ♦ Low Crosstalk: $< -93dB (50\Omega)$
- ♦ High Off-Isolation: < -96dB (50Ω)</p>

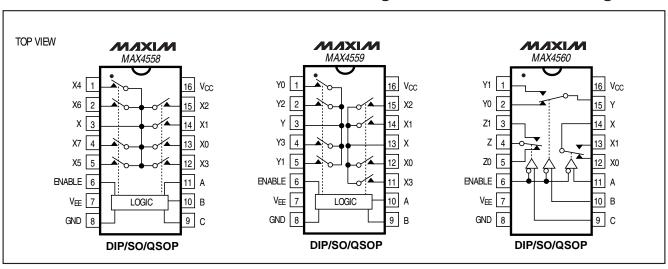
Ordering Information

PART	TEMP. RANGE	PIN-PACKAGE
MAX4558CEE	0℃ to +70℃	16 QSOP
MAX4558CSE	0℃ to +70℃	16 Narrow SO
MAX4558CPE	0℃ to +70℃	16 Plastic DIP

Ordering Information continued at end of data sheet.

Rail-to-Rail is a registered trademark of Nippon Motorola, Ltd.

Pin Configurations/Functional Diagrams



MIXIM

Maxim Integrated Products 1

ABSOLUTE MAXIMUM RATINGS

(Voltages referenced to VEE)
V _C C0.3V to +13V
Voltage into Any Terminal (Note 1) (VEE - 0.3V) to (VCC + 0.3V)
Continuous Current into Any Terminal±10mA
Peak Current, X, Y, Z, X_, Y_, Z_
(pulsed at 1ms, 10% duty cycle)±30mA
ESD per Method IEC 1000-4-2 (X, Y, Z, X_, Y_, Z_)
Air-Gap Discharge ±12kV
Contact Discharge±8kV
ESD per Method 3015.7
VCC, VEE, A, B, C, ENABLE, GND ±2.5kV
X, Y, Z, X_, Y_, Z±15kV

Continuous Power Dissipation ($T_A = +70^{\circ}$ C)	
QSOP (derate 8.00mW/℃ above +70℃)	640mW
Narrow SO (derate 8.70mW/℃ above +70	℃)696mW
DIP (derate 10.53mW/℃ above +70℃)	842mW
Operating Temperature Ranges	
MAX45C_E	0℃ to +70℃
MAX45E_E	40℃ to +85℃
Storage Temperature Range	65℃ to +150℃
Lead Temperature (soldering, 10sec)	+300℃

Note 1: Signals on any terminal exceeding V_{CC} or V_{EE} are clamped by internal diodes. Limit forward diode current to maximum current rating.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS—Dual ±5V Supplies

 $(V_{CC} = +4.5V \text{ to } +5.5V, V_{EE} = -4.5V \text{ to } -5.5V, V_{H} = +2.4V, V_{L} = +0.8V, T_{A} = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted. Typical values are at } T_{A} = +25\%.)$

PARAMETER	SYMBOL	CONDITIONS		TA	MIN	TYP (Note 2)	MAX	UNITS		
ANALOG SWITCH	ANALOG SWITCH									
Analog Signal Range	V _X _, V _Y _, V _Z _, V _X , V _Y , V _Z			C, E	V-		V+	V		
On-Resistance	Ron	V _{CC} = 4.5V; V _{EE} = -4.5V;		+25℃		110	160	Ω		
On-Nesistance	NON	IX , IY , $IZ = 1mA$; $VX_$, $VY_$, $VZ_$	= ±3V	C, E			180	52		
On-Resistance Match	ΔRon	VCC = 4.5V; VEE = -4.5V;		+25℃		2	6	Ω		
Between Channels (Note 3)	ΔIXON	I_X , I_Y , $I_Z = 1mA$; V_{X} , V_{Y} , V_{Z}	I_X , I_Y , $I_Z = 1mA$; V_{X} , V_{Y} , $V_{Z} = \pm 3V$				8	52		
On-Resistance Flatness	DEL ATIONS	V _{CC} = 4.5V; V _{EE} = -4.5V;		+25℃		3	8	Ω		
(Note 4)	RFLAT(ON)	I_X , I_Y , $I_Z = 1mA$; V_{X} , V_{Y} , V_{Z}	= -3V, 0V, 3V	C, E			10	32		
X_, Y_ , Z_ Off-Leakage	IX_(OFF), IY_(OFF),	V _{CC} = 5.5V; V _{EE} = -5.5V; V _X , V _Y , V _Z = 4.5V, -4.5V;		+25℃	-1	0.002	1	nA		
Current (Note 5)	I _{Z_(OFF)}	V_X , V_Y , $V_Z = -4.5V$, $4.5V$		C, E	-10		10	.,,		
		V 5.574.V 5.574	MAX4558	+25℃	-2	0.002	2			
X, Y, Z Off-Leakage Current	IX(OFF),	$V_{CC} = 5.5V; V_{EE} = -5.5V; V_{X}, V_{Y}, V_{Z} = 4.5V, -4.5V;$	W/ 04-1000	C, E	-20		20	nA		
(Note 5)	IZ(OFF)	Vx, Vy, Vz = -4.5V, 4.5V	MAX4559	+25℃	-1	0.002	1	1171		
	(- /		MAX4560	C, E	-10	0.002	10			
			MAX4558	+25℃	-2	0.002	2			
X, Y, Z On-Leakage Current	IX(ON),	$V_{CC} = 5.5V; V_{EE} = -5.5V; V_{X}, V_{Y}, V_{Z} = 4.5V, 4.5V;$	WIANASSO	C, E	-20		20	nA		
(Note 5)	l _{Y(ON)} , l _{Z(ON)}	Vχ_, VY_, VZ_ = 4.5V, 4.5V, Vx. VY. Vz = 4.5V4.5V	MAX4559	+25℃	-1	0.002	1	11/4		
	_(3)		MAX4560	C, E	-10	0.002	10			

ELECTRICAL CHARACTERISTICS—Dual ±5V Supplies (continued)

(VCC = +4.5V to +5.5V, VEE = -4.5V to -5.5V, V_{LH} = +2.4V, V_{LL} = +0.8V, T_{AL} = T_{MIN} to T_{MAX} , unless otherwise noted. Typical values are at T_{AL} = +25°C.)

PARAMETER	SYMBOL	CONDITIONS		TA	MIN	TYP (Note 2)	MAX)	UNITS	
DIGITAL I/O				1					
Input Logic High	VA_, VB_, VC_, VEN			C, E	2.4			V	
Input Logic Low	VA_, VB_, VC_, VEN			C, E			8.0	V	
Input Current Logic High or Low	VA_, VB_, VC_, VEN	V _A , V _B , V _C , V _{EN} = V _{CC} or 0		C, E	-1		1	μA	
POWER SUPPLY									
Power-Supply Range		VCC, VEE		C, E	±2		±6	V	
Supply Current,	Icc	$V_{CC} = 5.5V$; $V_{EE} = -5.5V$;		+25℃	-1		1	μA	
VCC or VEE	100	V_A , V_B , V_C , $V_{EN} = 0$ or V_{CC}		C, E	-10		10	μΛ	
SWITCH DYNAMIC CHARACT	ERISTICS								
Turn-On Time	ton	$Vx_{-}, Vy_{-}, Vz_{-} = 3V; RL = 300\Omega; CL = 35pF$	$2; C_L = 35pF;$	+25℃		90	150	ns	
rum on time	TON	Figure 1		C, E			175	113	
Turn-Off Time	toff	$V_{X_{-}}, V_{Y_{-}}, V_{Z_{-}} = 3V; R_{L} = 300\Omega$	$C_{L} = 35pF;$	+25℃		55	120	ns	
Turri On Time	UFF	Figure 1		C, E			150	113	
Address Transition Time	ttrans	$V_{X_{-}}, V_{Y_{-}}, V_{Z_{-}} = 3V; R_{L} = 300\Omega$	$C_{L} = 35pF;$	+25℃		90	150	ns	
Address Transition Time	TINANS	Figure 1		C, E			175	113	
Break-Before-Make Delay	topen	$V_{X_{-}}, V_{Y_{-}}, V_{Z_{-}} = 3V; R_{L} = 300\Omega$ Figure 2	$2; C_L = 35pF;$	+25℃	4	15		ns	
Charge Injection	Q	V_X , V_Y , $V_Z = 0$; $R_S = 0$; $C_L = 1$ Figure 3	nF;	+25℃		2.4		pC	
V _{X_} , V _{Y_} , V _{Z_} Off-Capacitance	CX_(OFF), CY_(OFF), CZ_(OFF)	Vx_, Vy_, Vz_ = 0; f = 1MHz; Figure 5		+25℃		2.5		pF	
	C _{X(OFF)} ,	., ., ., .,	MAX4558			10			
Vx, Vy, Vz Off-Capacitance	Cy(off),	V_X , V_Y , $V_Z = GND$; $f = 1MHz$; Figure 5	MAX4559	+25℃		6		pF	
	C _{Z(OFF)}	MAX4560		1		4			
		\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	MAX4558			15		pF	
Switch On-Capacitance	CON		MAX4559	+25℃		11			
		· ·=, · · J ··· · ·	MAX4560			9		1	

ELECTRICAL CHARACTERISTICS—Dual ±5V Supplies (continued)

(VCC = +4.5V to +5.5V, VEE = -4.5V to -5.5V, V_{H} = +2.4V, V_{L} = +0.8V, T_{A} = T_{MIN} to T_{MAX} , unless otherwise noted. Typical values are at T_{A} = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN TYP MAX (Note 2)	UNITS
Off-Isolation	Viso	$C_L = 15pF; R_L = 50\Omega; f = 100kHz; V_{X_,} V_{Y}, V_{Z} = 1V_{RMS}; Figure 4$	+25℃	-96	dB
Channel-to-Channel Crosstalk	Vст	$C_L = 15pF; R_L = 50\Omega; f = 100kHz; V_{X_,} V_{Y}, V_{Z} = 1V_{RMS}; Figure 4$	+25℃	-93	dB
Total Harmonic Distortion	THD	$R_L = 600\Omega$; V_{X} , V_{Y} , $V_{Z} = 5Vp-p$; $f = 20Hz$ to $20kHz$	+25℃	0.02	%
ESD SCR Positive Holding	lu.		+25℃	110	mA
Current	I _{H+}		+85℃	70	IIIA
ESD SCR Negative Holding	lH-		+25℃	95	mA
Current	H +8:	+85℃	65	11174	

ELECTRICAL CHARACTERISTICS—Single +5V Supply

(V_{CC} = +4.5V to +5.5V, V_{EE} = 0, V_H = +2.4V, V_L = +0.8V, T_A = T_{MIN} to T_{MAX}, unless otherwise noted. Typical values are at $T_A = +25$ °C.)

PARAMETER	SYMBOL	CONDITIONS		TA	MIN	TYP (Note 2)	MAX	UNITS
ANALOG SWITCH								
Analog Signal Range	Vx_, Vy_, Vz_, Vx, Vy, Vz			C, E	0		V+	V
On-Resistance	Ron	$V_{CC} = 4.5V$; I_X , I_Y , $I_Z = 1mA$;		+25℃		150	220	Ω
On-Nesistance	NON	Vx, Vy , $Vz = 3V$		C, E			350	52
On-Resistance Match Between Channels	ΔR _{ON}	V _{CC} = 4.5V; I _X , I _Y , I _Z = 1mA; V _X , V _Y , V _Z = 3V		+25℃		3	10	Ω
(Note 3, 6)	ZIVON			C, E			12	32
X_, Y_ , Z_ Off-Leakage	IX_(OFF), IY_(OFF),	$V_{CC} = 5.5V$; V_{X} , V_{Y} , $V_{Z} = 1V$,	4.5V,	+25℃	-1	0.002	1	nA
Current (Note 6)	I _{Z_(OFF)}	V_X , V_Y , $V_Z = 4.5V$, 1V		C, E	-10		10	
			MAX4558	+25℃	-2	0.002	2	
X, Y, Z Off-Leakage Current	IX(OFF),	$V_{CC} = 5.5V;$ V_X , V_Y , $V_Z = 1V$, 4.5V;	WAX4556	C, E	-20		20	nA
(Note 6)	l _{Y(OFF)} , l _{Z(OFF)}	$V_{X_{-}}, V_{Y_{-}}, V_{Z_{-}} = V_{V_{-}}, 4.5V_{+}$ $V_{X_{+}}, V_{Y_{+}}, V_{Z_{-}} = 4.5V_{+}, 1V_{-}$	MAX4559	+25℃	-1	0.002	1	IIA
	12(011)	170, 11, 12	MAX4560	C, E	-10		10	
			MAX4558	+25℃	-2	0.002	2	
X, Y, Z On-Leakage Current (Note 6)	IX(ON),	V _{CC} = 5.5V; V _X , V _Y , V _Z = 1V, 4.5V; V _X , V _Y , V _Z = 1V, 4.5V	WAAASSO	C, E	-20		20	nA
	ly(ON), lz(ON)		MAX4559	+25℃	-1	0.002	1	IIA
	2(011)	70 17 2 17, 1121	MAX4560	C, E	-10	0.002	10	

ELECTRICAL CHARACTERISTICS—Single +5V Supply (continued)

(VCC = +4.5V to +5.5V, VEE = 0, V_H = +2.4V, V_L = +0.8V, TA = TMIN to TMAX, unless otherwise noted. Typical values are at $T_A = +25$ °C.)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 2)	MAX	UNITS
DIGITAL I/O	1		•				
Input Logic High	VA_, VB_, VC_, VEN		C, E	2.4			V
Input Logic Low	VA_, VB_, VC_, VEN		C, E			0.8	V
Input Current Logic High or Low	VA_, VB_, VC_, VEN	V _A , V _B , V _C , V _{EN} = V _{CC} or 0	C, E	-1		1	μA
SWITCH DYNAMIC CHARAC	TERISTICS	(Note 6)					
Turn-On Time	ton	$V_{X_{-}}, V_{Y_{-}}, V_{Z_{-}} = 3V; R_{L} = 300\Omega; C_{L} = 35pF;$	+25℃		110	250	ns
Turn-On Time	Fi	Figure 1	C, E			300	113
Turn-Off Time	toff	V_{X} , V_{Y} , V_{Z} = 3V; R_L = 300 Ω ; C_L = 35pF; Figure 1	+25℃		50	150	ns
Turr on Time	UFF		C, E			200	113
Address Transition Time	tTRANS	$V_{X_{-}}, V_{Y_{-}}, V_{Z_{-}} = 3V; R_{L} = 300\Omega; C_{L} = 35pF;$	+25℃		110	250	ns
Address Transition Time	TRANS	Figure 1	C, E			300	113
Break-Before-Make Delay	topen	$V_{X_}$, $V_{Y_}$, $V_{Z_}$ = 3V; R_L = 300 Ω ; C_L = 35pF; Figure 3	C, E	10			ns
Charge Injection	Q	V_X , V_Y , $V_Z = 2.5V$; $R_S = 0$; $C_L = 1nF$; Figure 3	+25℃		1		pC
POWER SUPPLY							I
V _{CC} Supply Current	loo	Voc - 5 5 // Vou Vou Vou Vou - 0 or Voc	+25℃	-1		1	
VCC Supply Current	Icc	$V_{CC} = 5.5V$; V_{AH} , V_{BH} , V_{CH} , $V_{EN} = 0$ or V_{CC}	C, E	-10		10	μA
Power-Supply Range		VCC, VEE	C, E	+2		+12	V

ELECTRICAL CHARACTERISTICS—Single +3V Supply

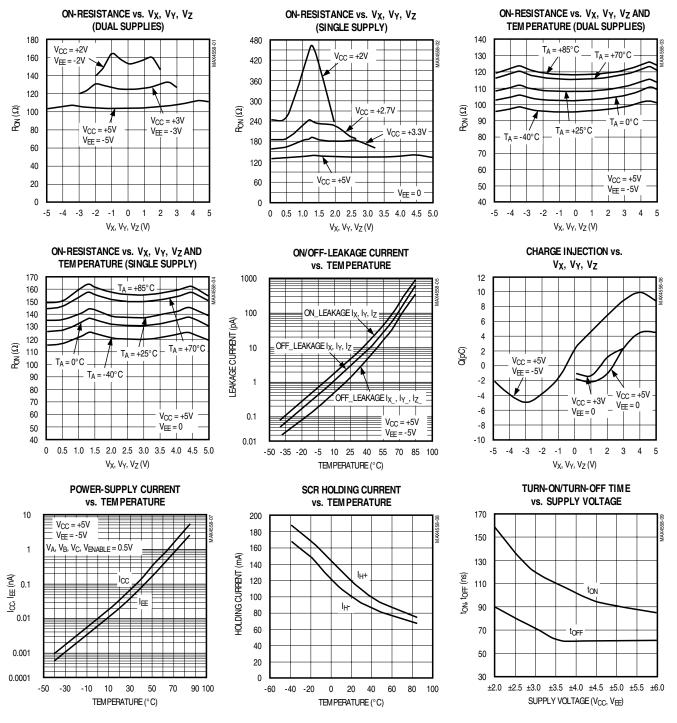
(VCC = +2.7V to +3.6V, V_H = +2.0V, V_L = +0.8V, TA = TMIN to TMAX, unless otherwise noted. Typical values are at TA = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 2	MAX)	UNITS
ANALOG SWITCH				ı			I
On-Resistance	Ron	V _C C = 2.7V; I _X , I _Y , I _Z = 0.1mA;	+25℃		220	400	Ω
On-Resistance	NON	V_X , V_Y , $V_Z = 1.5V$	C, E			450	1 52
DIGITAL I/O							
Input Logic High	VA_, VB_, VC_, VEN		C, E	1.5			V
Input Logic Low	VA_, VB_, VC_, VEN		C, E			0.5	V
Input Current Logic High or Low	VA_, VB_, VC_, VEN	VA, VB, VC, VEN = VCC or 0	C, E	-1		1	μA
SWITCH DYNAMIC CHARAC	CTERISTICS	(Note 6)		•			•
Turn-On Time	ton	$V_{X_{-}}, V_{Y_{-}}, V_{Z_{-}} = 1.5V; R_{L} = 1k\Omega;$	+25℃		180	350	ns
Turn-Off fillie	ION	C _L = 35pF; Figure 1	C, E			400	113
Turn-Off Time	toff	$V_{X_{-}}, V_{Y_{-}}, V_{Z_{-}} = 1.5V; R_{L} = 1k\Omega;$	+25℃		90	250	ns
Turri Ori Time	IOFF	C _L = 35pF; Figure 1	C, E			300	113
Address Transition Time	tTRANS	V_{X} , V_{Y} , V_{Z} = 1.5 V ; R_L = 1 $k\Omega$;	+25℃		180	350	ns
Address Transition Time	TRANS	C _L = 35pF; Figure 1	C, E			400	113
Break-Before-Make Delay	tOPEN	V_{X} , V_{Y} , V_{Z} = 1.5 V ; R_L = 1 $k\Omega$; C_L = 35pF; Figure 2	C, E	1.5			ns
Charge Injection	Q	V_X , V_Y , $V_Z = 1.5V$; $R_S = 0$; $C_L = 1nF$; Figure 3	+25℃		0.5		pC
POWER SUPPLY			•				
V _{CC} Supply Current	Icc	V _{CC} = 3.6V; V _A , V _B , V _C , V _{EN} = 0 or V _{CC}	+25℃	1	0.5	1	ПΑ
VCC Supply Cullent	icc	VCC = 3.0V, VA_, VB_, VC_, VEN = 0.01 VCC	C, E	-10		10	μA

- Note 2: The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.
- **Note 3:** $\Delta R_{ON} = R_{ON(MAX)} R_{ON(MIN)}$.
- **Note 4:** Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges; i.e., Von = 3V to 0 and 0 to -3V.
- Note 5: Leakage parameters are 100% tested at the maximum-rated hot operating temperature and are guaranteed by correlation at T_A = +25℃.
- Note 6: Guaranteed by design, not production tested.

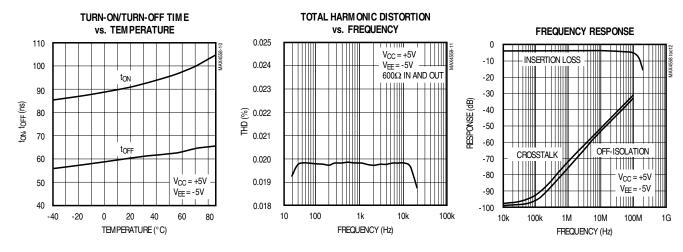
Typical Operating Characteristics

 $(V_{CC} = +5V, V_{EE} = -5V, T_A = +25^{\circ}C, unless otherwise noted.)$



Typical Operating Characteristics (continued)

 $(V_{CC} = +5V, V_{EE} = -5V, T_A = +25$ °C, unless otherwise noted.)



Pin Description

PIN			FUNOTION		
MAX4558	MAX4559	MAX4560	NAME	FUNCTION	
1, 2, 4, 5, 12–15	_	_	X0-X7	Analog Switch Inputs 0–7	
3	_	_	Х	Analog Switch Output	
_	11, 12, 14, 15	_	X0, X1, X2, X3	Analog Switch "X" Inputs 0–3	
_	13	14	Х	Analog Switch "X" Output	
_	_	13	X1	Analog Switch "X" Normally Open Input	
_	_	12	X0	Analog Switch "X" Normally Closed Input	
_	_	1	Y1	Analog Switch "C" Normally Open Input	
_	_	2	Y0	Analog Switch "C" Normally Closed Input	
6	6	6	ENABLE	Digital Enable Input. Connect to GND to enable device. Drive high to set all switches off.	
7	7	7	VEE	Negative Analog Supply Voltage Input. Connect to GND for single-supply operation.	
8	8	8	GND	Ground	
11	10	11	А	Digital Address "A" Input	
10	9	10	В	Digital Address "B" Input	
9	_	9	С	Digital Address "C" Input	
_	1, 2, 4, 5	_	Y0, Y1, Y2, Y3	Analog Switch "Y" Inputs 0–3	
_	3	15	Y	Analog Switch "Y" Output	
_	_	5	Z0	Analog Switch "Z" Normally Closed Input	
_	_	3	Z1	Analog Switch "Z" Normally Open Input	
_	_	4	Z	Analog Switch "Z" Output	
16	16	16	Vcc	Positive Analog and Digital Supply Voltage Input	

NIXIN

Detailed Description

The MAX4558/MAX4559/MAX4560 are ESD protected (per IEC 1000-4-2) at their X, Y, Z output pins and X_, Y_, Z_ input pins. These ICs feature on-chip bidirectional silicon-controlled rectifiers (SCRs) between the protected pins and GND. The SCRs are normally off and have a negligible effect on the switches' performance. During an ESD strike, the voltages at the protected pins go Beyond-the-Rails™, causing the corresponding SCR(s) to turn on in a few nanoseconds. This bypasses the surge current safely to ground. This protection method is superior to using diode clamps to the supplies. Unless the supplies are very carefully decoupled through low-ESR capacitors, the ESD current through a diode clamp could cause a significant spike in the supplies, which might damage or compromise the reliability of any other chip powered by those same supplies.

In addition to the SCRs at the ESD-protected pins, these devices provide internal diodes connected to the supplies. Resistors placed in series with these diodes limit the current flowing into the supplies during an ESD strike. The diodes protect the X, Y, Z and X_, Y_, Z_pins from overvoltages due to improper power-supply sequencing.

Once the SCR turns on because of an ESD strike, it remains on until the current through it falls below its "holding current." The holding current is typically 110mA in the positive direction (current flowing into the pin) and 95mA in the negative direction at room temperature (see SCR Holding Current vs. Temperature in the *Typical Operating Characteristics*). The system should be designed so that any sources connected to

the X, Y, Z or X_, Y_, Z_ pins are current limited to a value below the holding current. This ensures that the SCR turns off and normal operation resumes after an ESD event.

Keep in mind that the holding currents vary significantly with temperature; they drop to 70mA (typ) in the positive direction and 65mA (typ) in the negative direction, at +85°C worst case. To guarantee turn-off of the SCRs under all conditions, current limit the sources connected to these pins to not more than half of these typical values. When the SCR is latched, the voltage across it is about ±3V, depending on the polarity of the pin current. The supply voltages do not affect the holding currents appreciably. When one or more SCRs turn on because of an ESD event, all switches in the part turn off to prevent current through the switch(es) from sustaining latchup.

Even though most of the ESD current flows to GND through the SCRs, a small portion of it goes into the supplies. Therefore, it is a good idea to bypass the supply pins with 100nF capacitors to the ground plane.

_Applications Information

ESD Protection

The MAX4558/MAX4559/MAX4560 are characterized for protection to the following:

- · ±15kV using the Human Body Model
- ±8kV using the Contact Discharge method specified in IEC 1000-4-2 (formerly IEC 801-2)
- ±12kV using the Air-Gap Discharge method specified in IEC 1000-4-2 (formerly IEC 801-2).

Beyond-the-Rails is a trademark of Maxim Integrated Products.

Table 1. Truth Table/Switch Programming

ENABLE		SELECT INPUTS			ON SWITCHES			
INPUT	C*	В	Α	MAX4558	MAX4559	MAX4560		
Н	Х	X	Х	All switches open	All switches open	All switches open		
L	L	L	L	X-X0	X-X0, Y-Y0	X-X0, Y-Y0, Z-Z0		
L	L	L	Н	X-X1	X-X1, Y-Y1	X-X1, Y-Y0, Z-Z0		
L	L	Н	L	X-X2	X-X2, Y-Y2	X-X0, Y-Y1, Z-Z0		
L	L	Н	Н	X-X3	X-X3, Y-Y3	X-X1, Y-Y1, Z-Z0		
L	Н	L	L	X-X4	X-X0, Y-Y0	X-X0, Y-Y0, Z-Z1		
L	Н	L	Н	X-X5	X-X1, Y-Y1	X-X1, Y-Y0, Z-Z1		
L	Н	Н	L	X-X6	X-X2, Y-Y2	X-X0, Y-Y1, Z-Z1		
L	Н	Н	Н	X-X7	X-X3, Y-Y3	X-X1, Y-Y1, Z-Z1		

X = Don't care * C not present on MAX4559.

Note: Input and output pins are identical and interchangeable. Either may be considered an input or output; signals pass equally well in either direction.



ESD Test Conditions

ESD performance depends on several conditions. Contact Maxim for a reliability report that documents test setup, methodology, and results.

Human Body Model

Figure 6 shows the Human Body Model, and Figure 7 shows the current waveform it generates when discharged into a low impedance. This model consists of a 100pF capacitor charged to the ESD voltage of interest, which is then discharged into the test device through a $1.5 \mathrm{k}\Omega$ resistor.

Power-Supply Considerations

The MAX4558/MAX4559/MAX4560 are typical of most CMOS analog switches. They have three supply pins: VCC, VEE, and GND. VCC and VEE drive the internal CMOS switches and set the limits of the analog voltage on every switch. Internal reverse ESD-protection diodes connect between each analog signal pin and both VCC and VEE. If any analog signal exceeds VCC or VEE, one of these diodes conducts. The only currents drawn from VCC or VEE during normal operation are the leakage currents of these ESD diodes.

Although the ESD diodes on a given signal pin are identical and therefore fairly well balanced, they are reverse biased differently. Each is biased by either VCC or VEE and the analog signal. Their leakage currents vary as the signal varies. The difference in the two diode leakages to the VCC and VEE pins constitutes the analog signal-path leakage current. All analog leakage current flows between each input and one of the supply

terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of either the same or opposite polarity.

VCC and GND power the internal logic and logic-level translators, and set the input logic limits. The logic-level translators convert the logic levels into switched VCC and VEE signals to drive the gates of the analog switch. This drive signal is the only connection between the logic supplies and logic signals and the analog supplies. VCC and VEE have ESD-protection diodes to GND.

The logic-level thresholds are TTL/CMOS compatible when V_{CC} is +5V. As V_{CC} rises, the threshold increases slightly. When V_{CC} reaches +12V, the threshold is about 3.1V (above the TTL-guaranteed high-level minimum of 2.4V, but still compatible with CMOS outputs).

High-Frequency Performance

In 50Ω systems, signal response is reasonably flat up to 50MHz (see *Typical Operating Characteristics*). Above 20MHz, the on response has several minor peaks that are highly layout dependent. The problem is not turning the switch on, but turning it off. The off-state switch acts like a capacitor and passes higher frequencies with less attenuation. At 1MHz, off-isolation is about -68dB in 50Ω systems, becoming worse (approximately 20dB per decade) as the frequency increases. Higher circuit impedance also degrades off-isolation. Adjacent channel attenuation is about 3dB above that of a bare IC socket and is entirely due to capacitive coupling.

____ /N/IXI/VI

_Test Circuits/Timing Diagrams

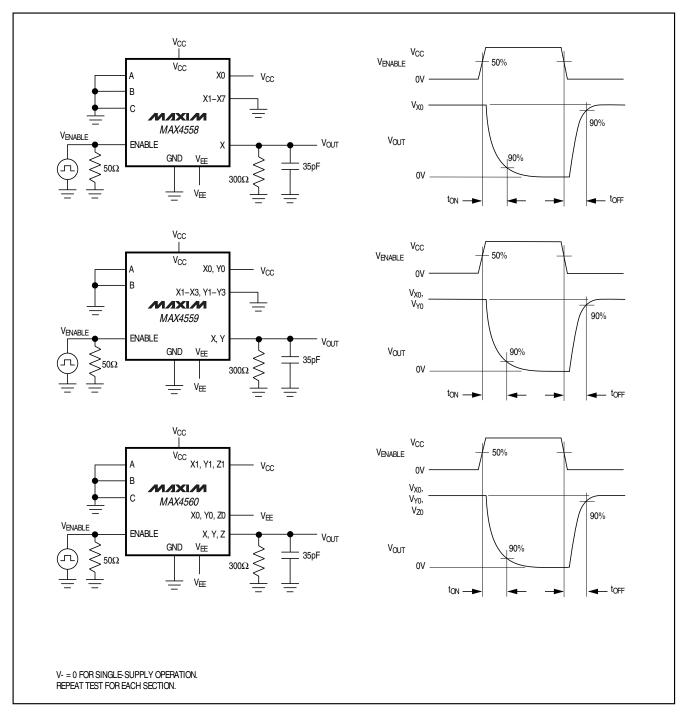


Figure 1. Switching Times

Test Circuits/Timing Diagrams (continued)

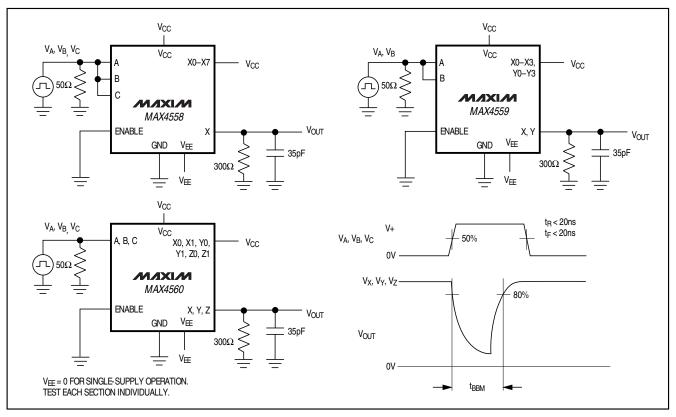


Figure 2. Break-Before-Make Interval

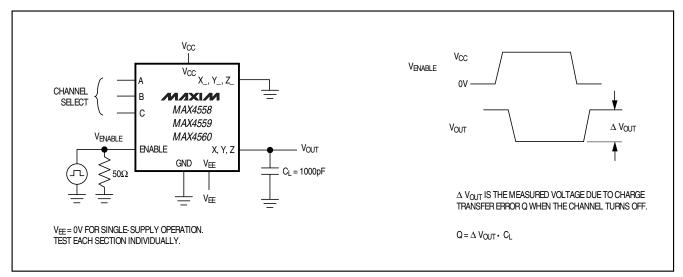


Figure 3. Charge Injection

Test Circuits/Timing Diagrams (continued)

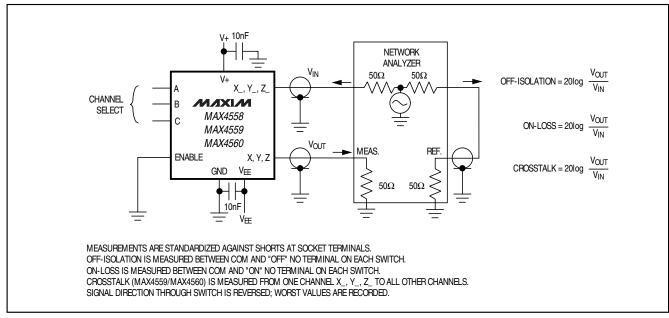


Figure 4. Off-Isolation/On-Channel Bandwidth and Crosstalk

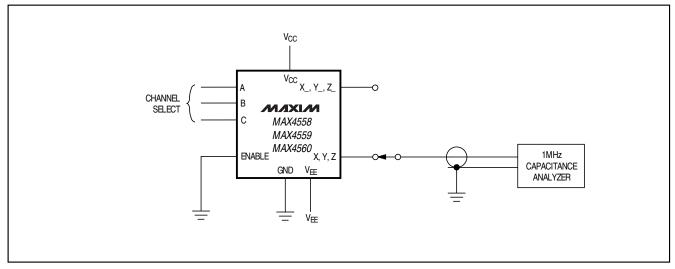


Figure 5. Channel Off/On-Capacitance

Test Circuits/Timing Diagrams (continued)

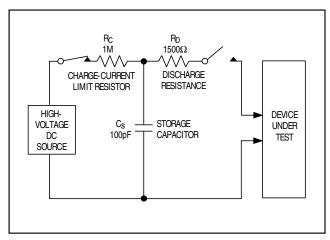


Figure 6. Human Body ESD Test Model

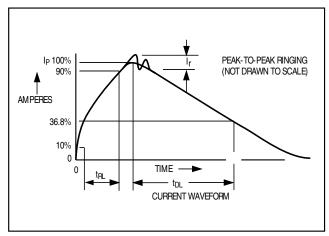


Figure 7. Human Body Model Current Waveform

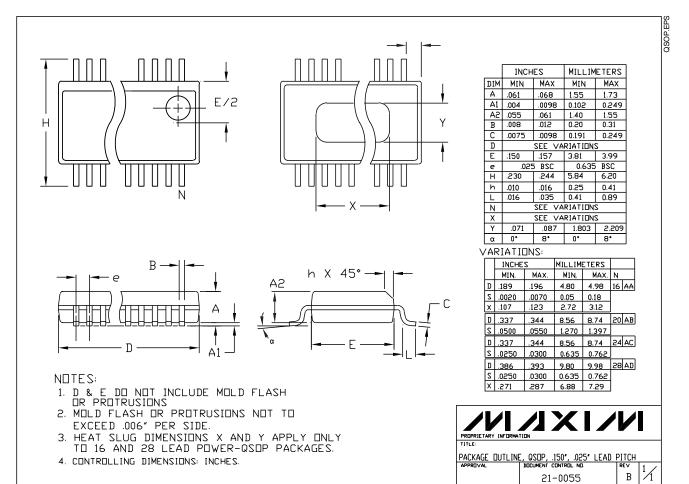
_Ordering Information (continued)

PART	TEMP. RANGE	PIN-PACKAGE
MAX4558EEE	-40℃ to +85℃	16 QSOP
MAX4558ESE	-40℃ to +85℃	16 Narrow SO
MAX4558EPE	-40℃ to +85℃	16 Plastic DIP
MAX4559CEE	0℃ to +70℃	16 QSOP
MAX4559CSE	0℃ to +70℃	16 Narrow SO
MAX4559CPE	0℃ to +70℃	16 Plastic DIP
MAX4559EEE	-40℃ to +85℃	16 QSOP
MAX4559ESE	-40℃ to +85℃	16 Narrow SO
MAX4559EPE	-40℃ to +85℃	16 Plastic DIP
MAX4560CEE	0℃ to +70℃	16 QSOP
MAX4560CSE	0℃ to +70℃	16 Narrow SO
MAX4560CPE	0℃ to +70℃	16 Plastic DIP
MAX4560EEE	-40℃ to +85℃	16 QSOP
MAX4560ESE	-40℃ to +85℃	16 Narrow SO
MAX4560EPE	-40℃ to +85℃	16 Plastic DIP

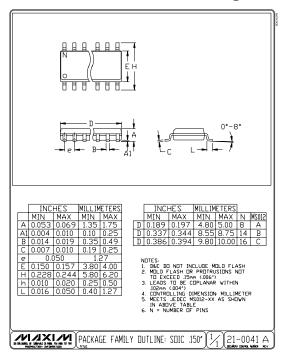
Chip Information

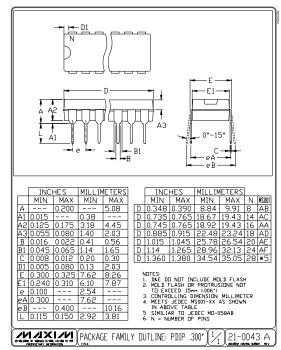
TRANSISTOR COUNT: 221

Package Information



Package Information (continued)





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